Silicon PNP Power Transistors 2N6285 2N6286 2N6287

DESCRIPTION

- With TO-3 package
- Complement to type 2N6282/6283/6284
- High DC current gain
- DARLINGTON

APPLICATIONS

- For use in general-purpose amplifier and low-frequency switching applications

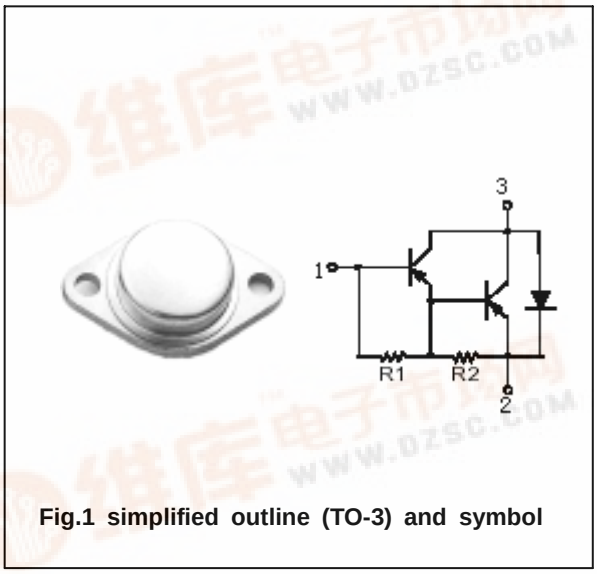

Fig.1 simplified outline (TO-3) and symbol

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings(Ta=℃)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2N6285	Open emitter	-60	V
		2N6286		-80	
		2N6287		-100	
V_{CEO}	Collector-emitter voltage	2N6285	Open base	-60	V
		2N6286		-80	
		2N6287		-100	
V_{EBO}	Emitter-base voltage		Open collector	-5	V
I_C	Collector current			-20	A
I_{CM}	Collector current-peak			-40	A
I_B	Base current			-0.5	A
P_D	Total Power Dissipation		T_C=25℃	160	W
T_j	Junction temperature			200	℃
T_{stg}	Storage temperature			-65~200	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j\text{-}c}$	Thermal resistance junction to case	1.09	℃/W

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	2N6285	I_C=-0.2A ;I_B=0	-60			V
		2N6286		-80			
		2N6287		-100			
$V_{CEsat-1}$	Collector-emitter saturation voltage		I_C=-10A; I_B=-40mA			-2.0	V
$V_{CEsat-2}$	Collector-emitter saturation voltage		I_C=-20A ;I_B=-200mA			-3.0	V
V_{BEsat}	Base-emitter saturation voltage		I_C=-20A ;I_B=-200mA			-4.0	V
V_{BE}	Base-emitter on voltage		I_C=-10A ; V_{CE}=-3V			-2.8	V
I_{CEO}	Collector cut-off current	2N6285	V_{CE}=-30V; I_B=0			-1.0	mA
		2N6286	V_{CE}=-40V; I_B=0				
		2N6287	V_{CE}=-50V; I_B=0				
I_{CEX}	Collector cut-off current	2N6285	V_{CE}=-60V; V_{BE}=-1.5V T_C=150℃			-0.5 -5.0	mA
		2N6286	V_{CE}=-80V; V_{BE}=-1.5V T_C=150℃			-0.5 -5.0	
		2N6287	V_{CE}=-100V; V_{BE}=-1.5V T_C=150℃			-0.5 -5.0	
I_{EBO}	Emitter cut-off current		V_{EB}=-5V; I_C=0			-2.0	mA
h_{FE-1}	DC current gain		I_C=-10A ; V_{CE}=-3V	750		18000	
h_{FE-2}	DC current gain		I_C=-20A ; V_{CE}=-3V	100			
C_{OB}	Output capacitance		I_E=0; V_{CB}=-10V;f=1MHz			600	pF

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PACKAGE OUTLINE

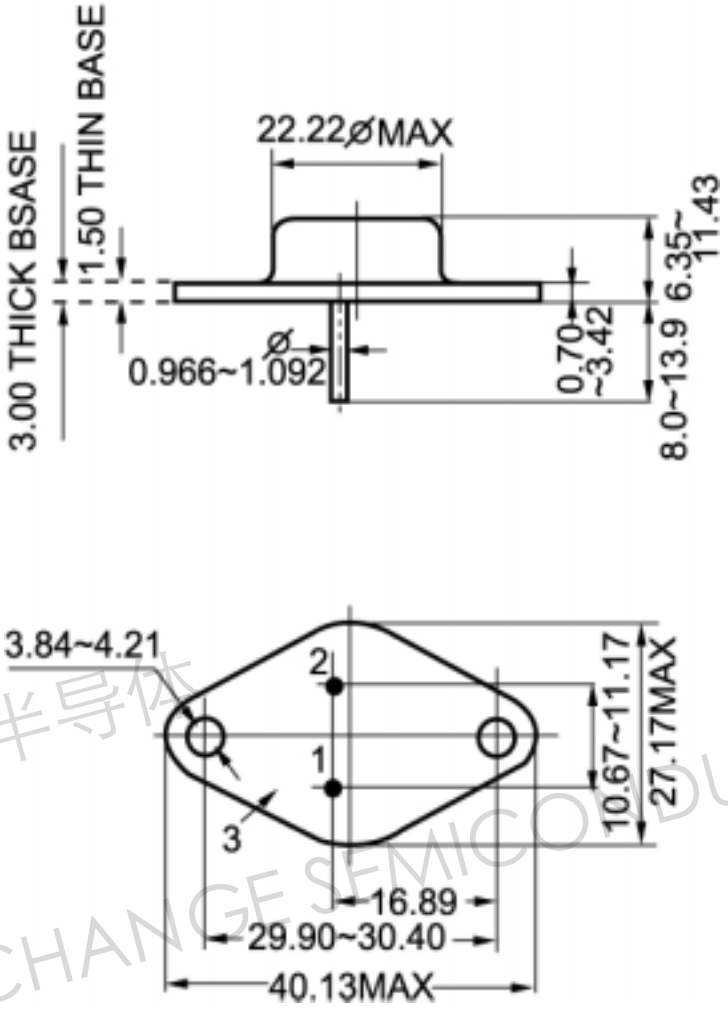

Fig.2 outline dimensions (unindicated tolerance:±0.10mm)